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# TRISO Fuel Performance Modeling in Bison

Modeling of TRISO coating layer fracture due to buffer debonding

**DOE ART Gas-Cooled Reactor (GCR) Review Meeting**

Virtual Meeting

July 25 – 27, 2023

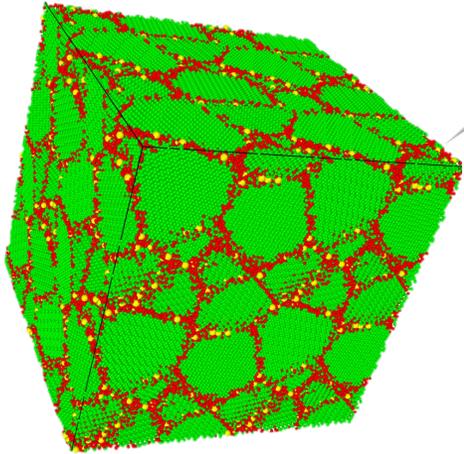




# Outlines

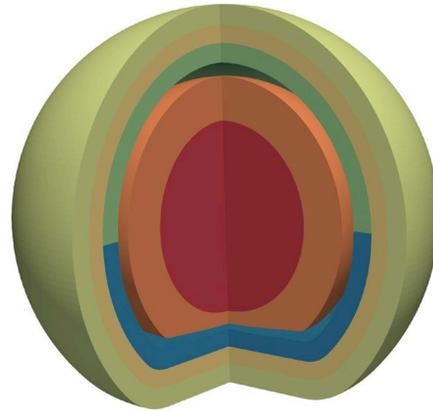
- Background and overview of BISON
- BISON debonding modeling
- Coating layer fracture modeling
- Buffer partial debonding

# BISON Overview



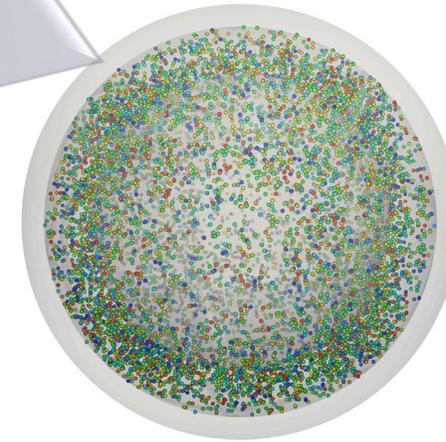
## Lower-length scale modeling

- **Fission gas release model:**  
Xe, Kr diffusivity in UCO
- **Fission product diffusivity:**  
Silver diffusion in SiC, Pd Penetration



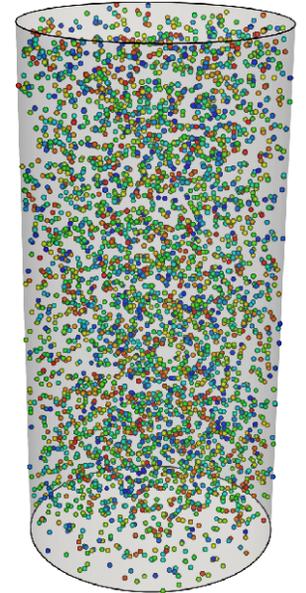
## TRISO particle

- **Thermal-mechanical modeling**
  - **Failure analysis:** asphericity, IPyC cracking and debonding
- **Fission product diffusion through layers**

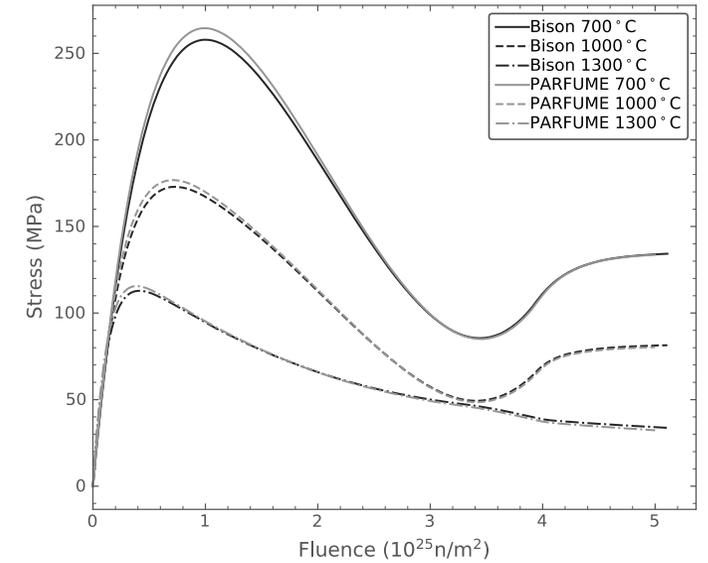
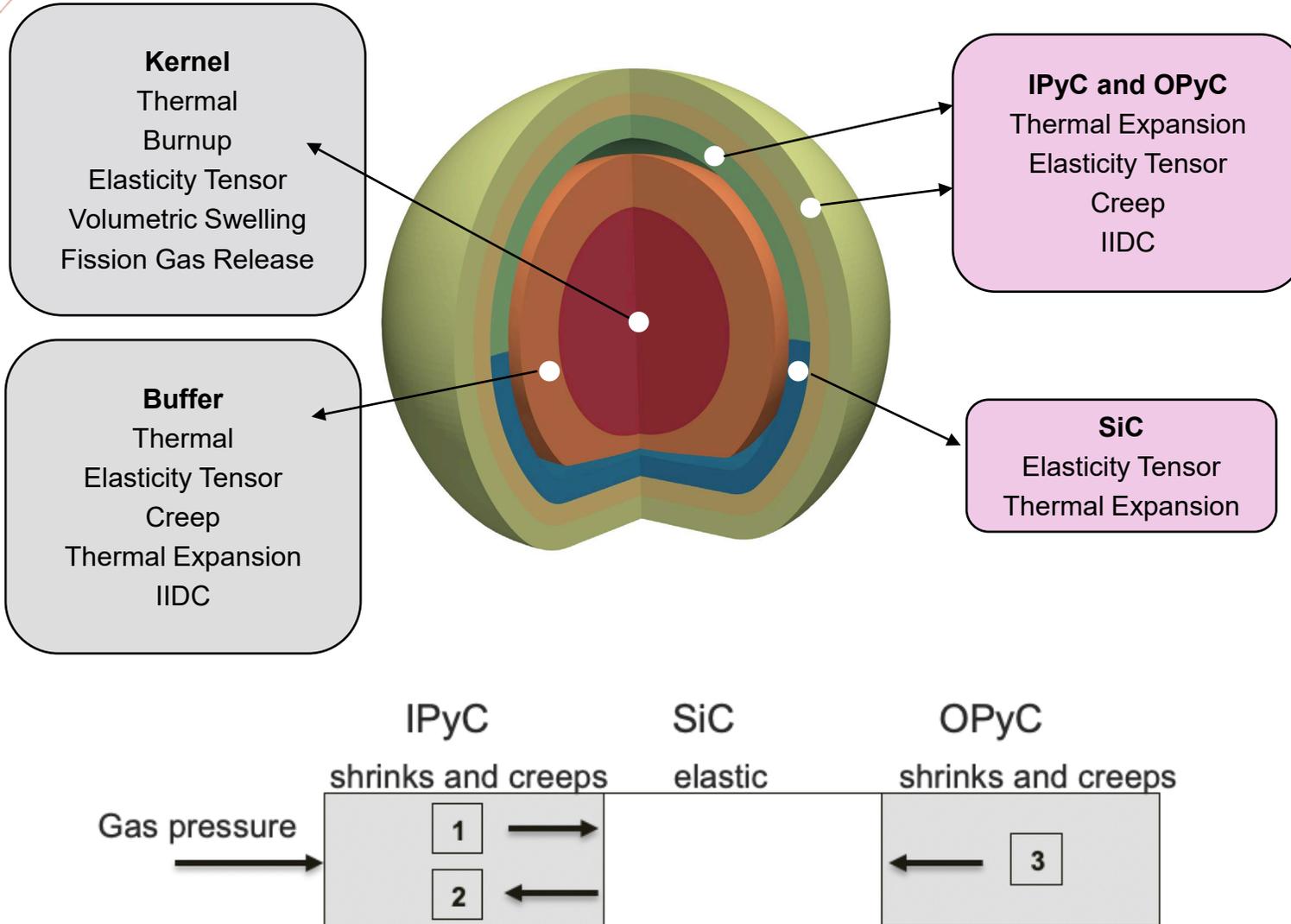


## Pebble and Compact modeling

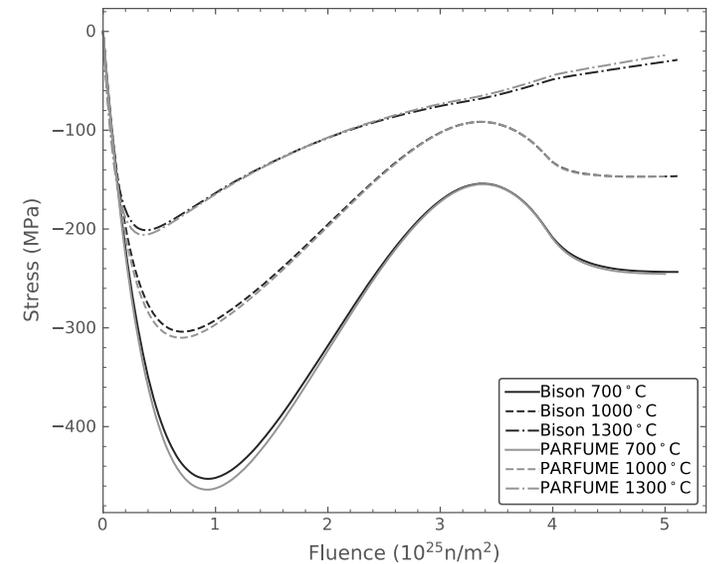
- **Failure probability calculation:**  
Monte Carlo and Fast Integration Approach
- **Fission product diffusion through matrix**
- **Particle-Matrix interaction**



# TRISO Fuel Particle Modeling



Tangential stress in IPyC



Tangential stress in SiC

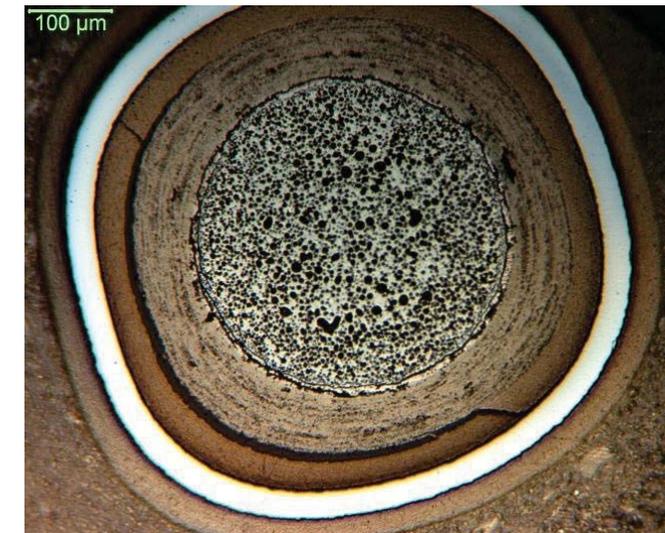
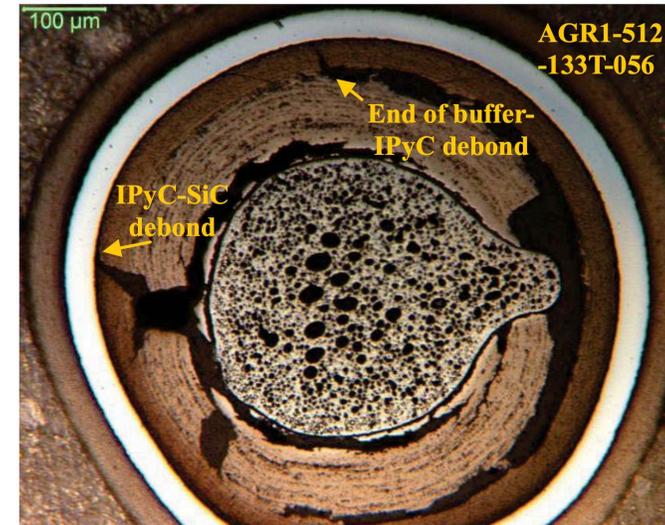
# Coating layers debonding

## Partial debonding of the IPyC from the SiC

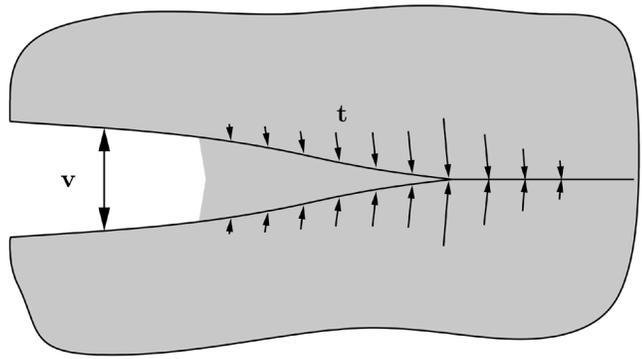
- ❑ Partial debonding between the IPyC and the SiC has also been observed in PIE of the NP-MHTGR fuel particles.
- ❑ During irradiation, shrinkage of the IPyC layer induces a radial tensile stress at the interface between the IPyC and SiC layer.
- ❑ If the stress exceeds the bond strength between layers, then debonding of the IPyC from the SiC occurs.
- ❑ A stress concentration occurs in the SiC layer at the tip of the debonded region, containing tensile stress components that could contribute to failure of the SiC.

## Buffer-IPyC partial debonding in AGR-1

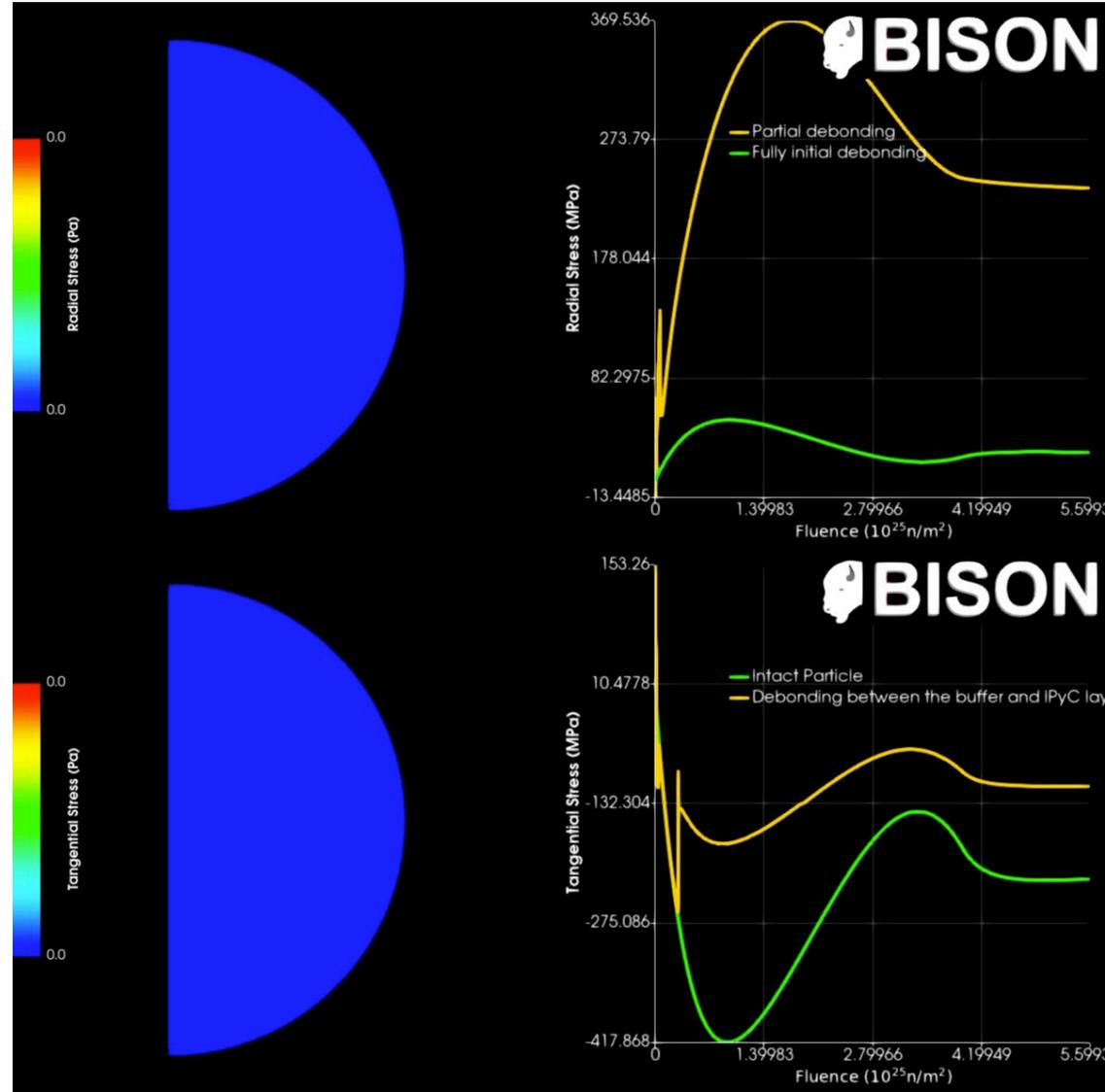
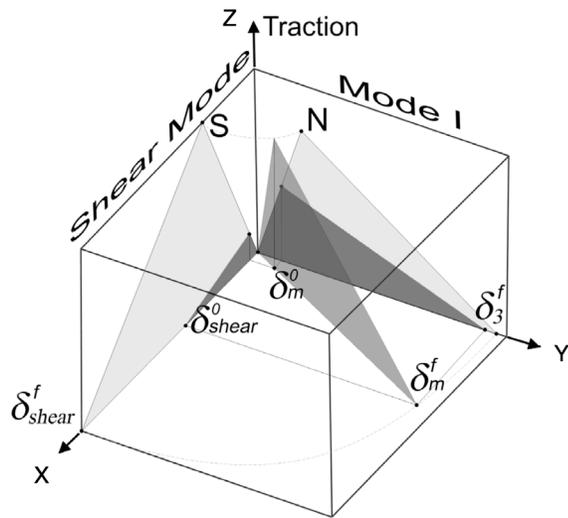
- ❑ Buffer-IPyC partial debonding were found with intermediate frequency in AGR-1 compacts and it can lead to IPyC cracking and separation from SiC layer.
- ❑ Allows localized attack of SiC layer by fission products (especially Pd)
- ❑ Pd attack can eventually result in loss of FP retention by SiC layer.
- ❑ Degradation is worse at higher safety test temperatures



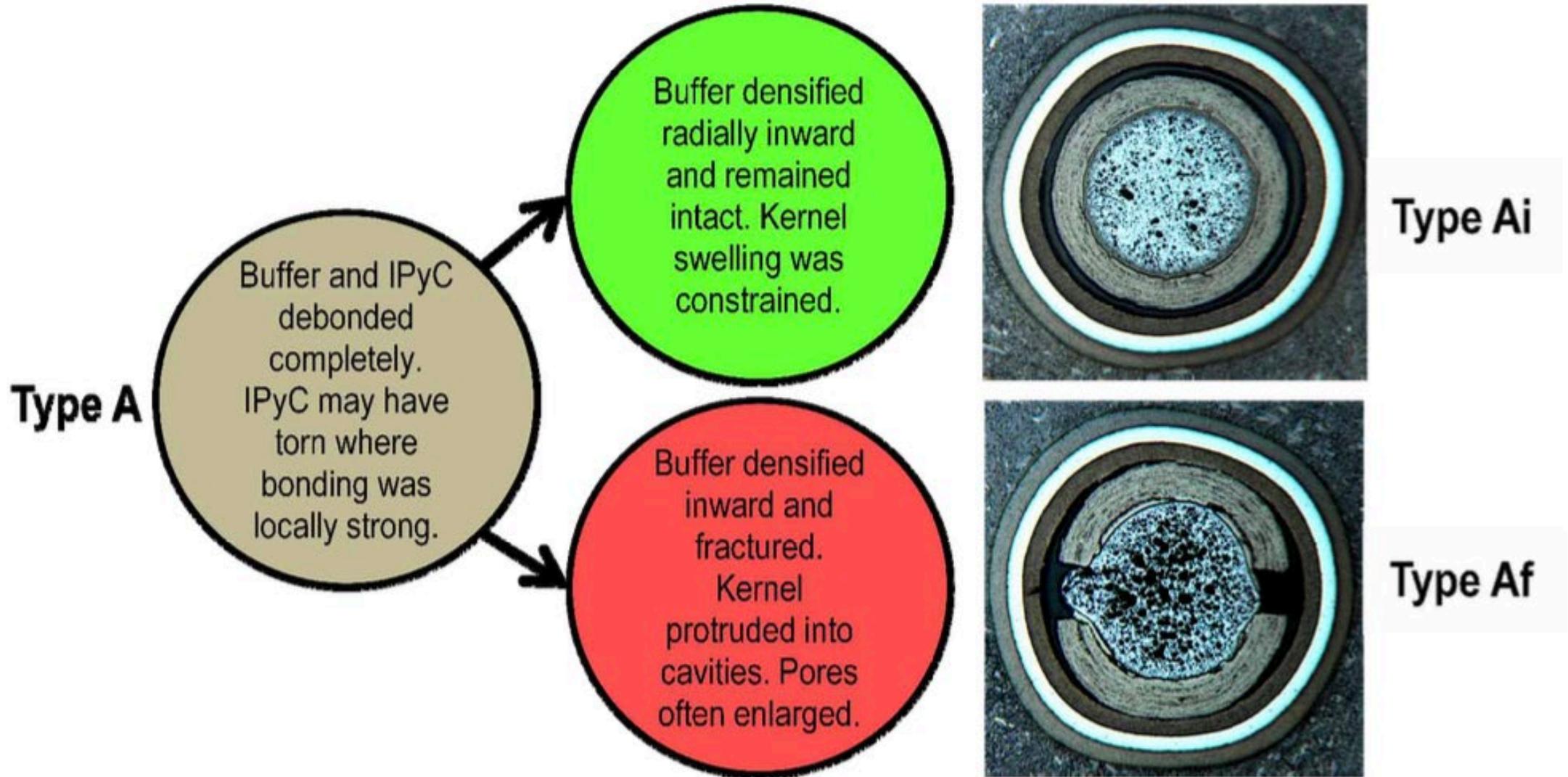
# Debonding with cohesive-zone method



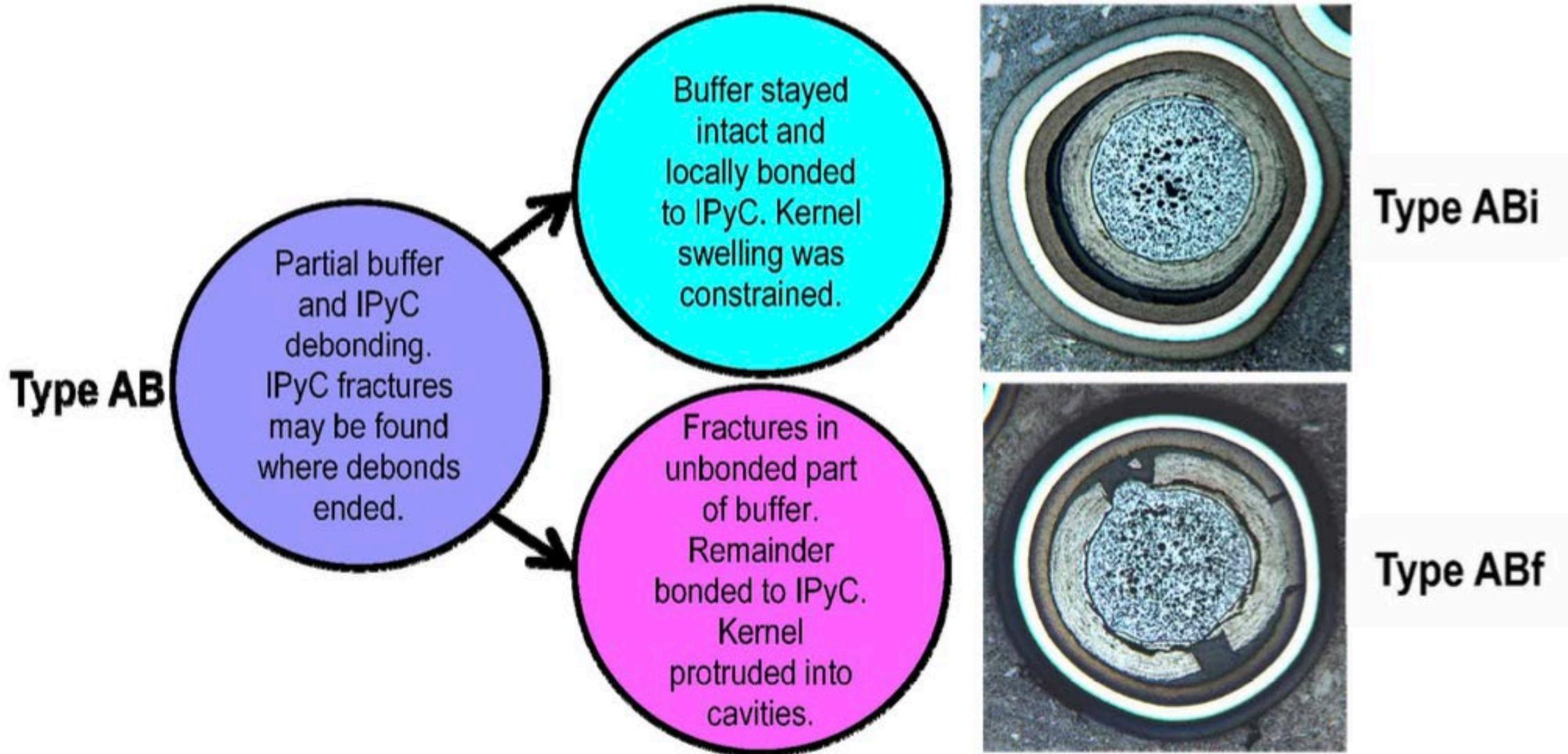
traction free | debonding | perfect bond



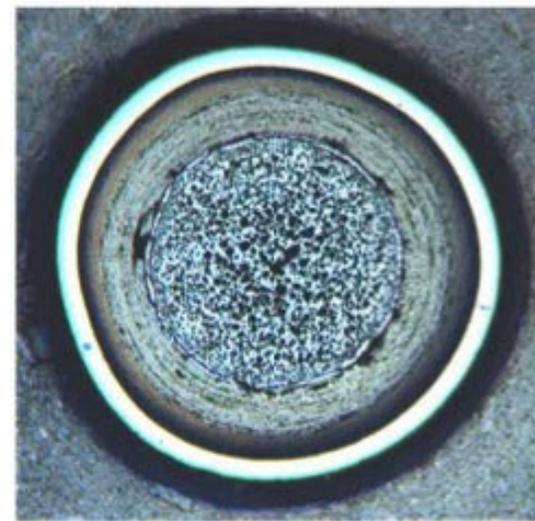
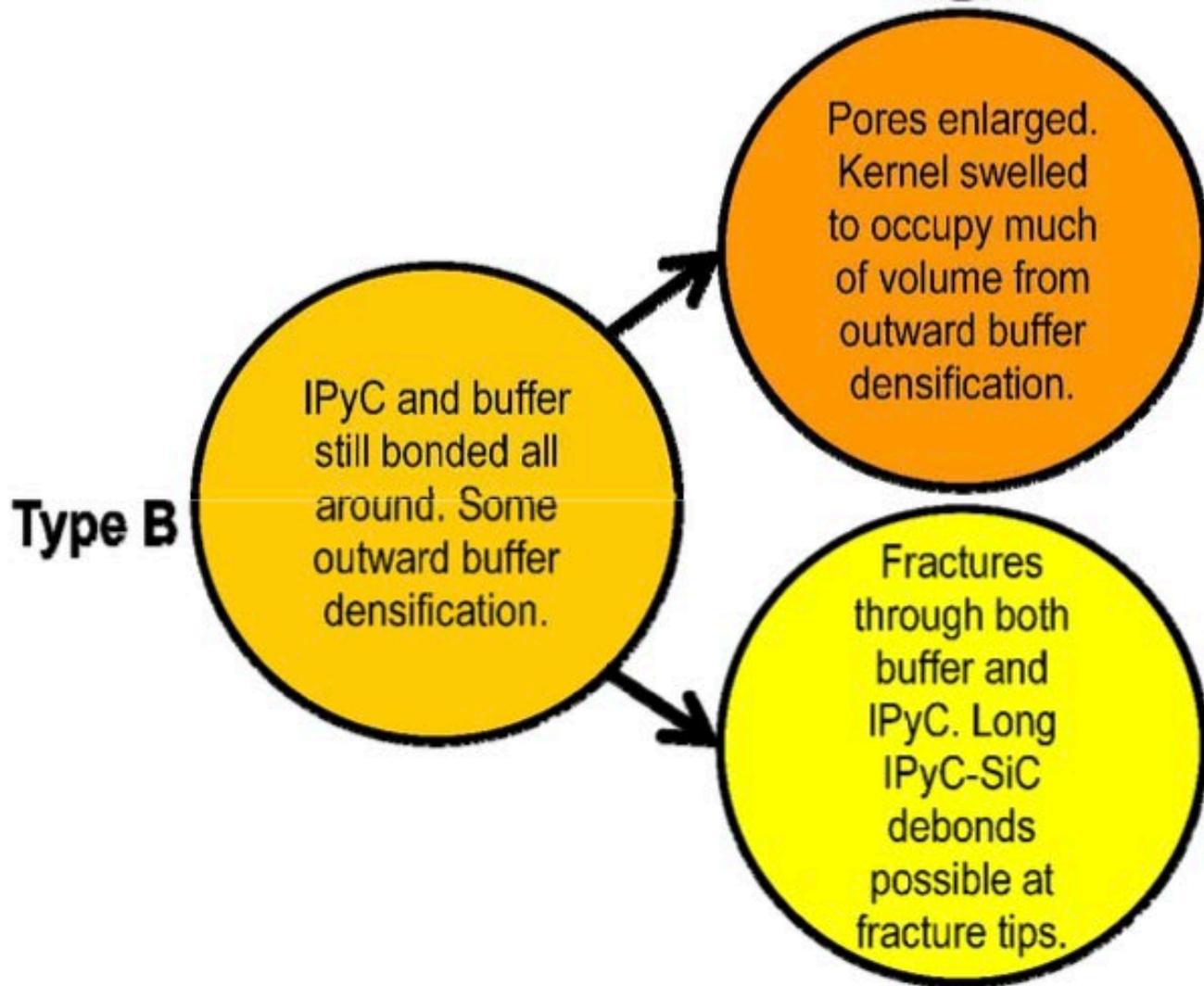
# Fracture types observed in AGR-1 – Type A



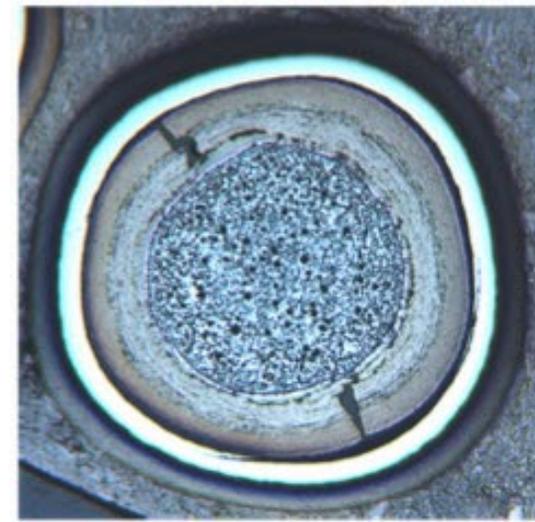
# Fracture types observed in AGR-1 – Type AB



# Fracture types observed in AGR-1 – Type B

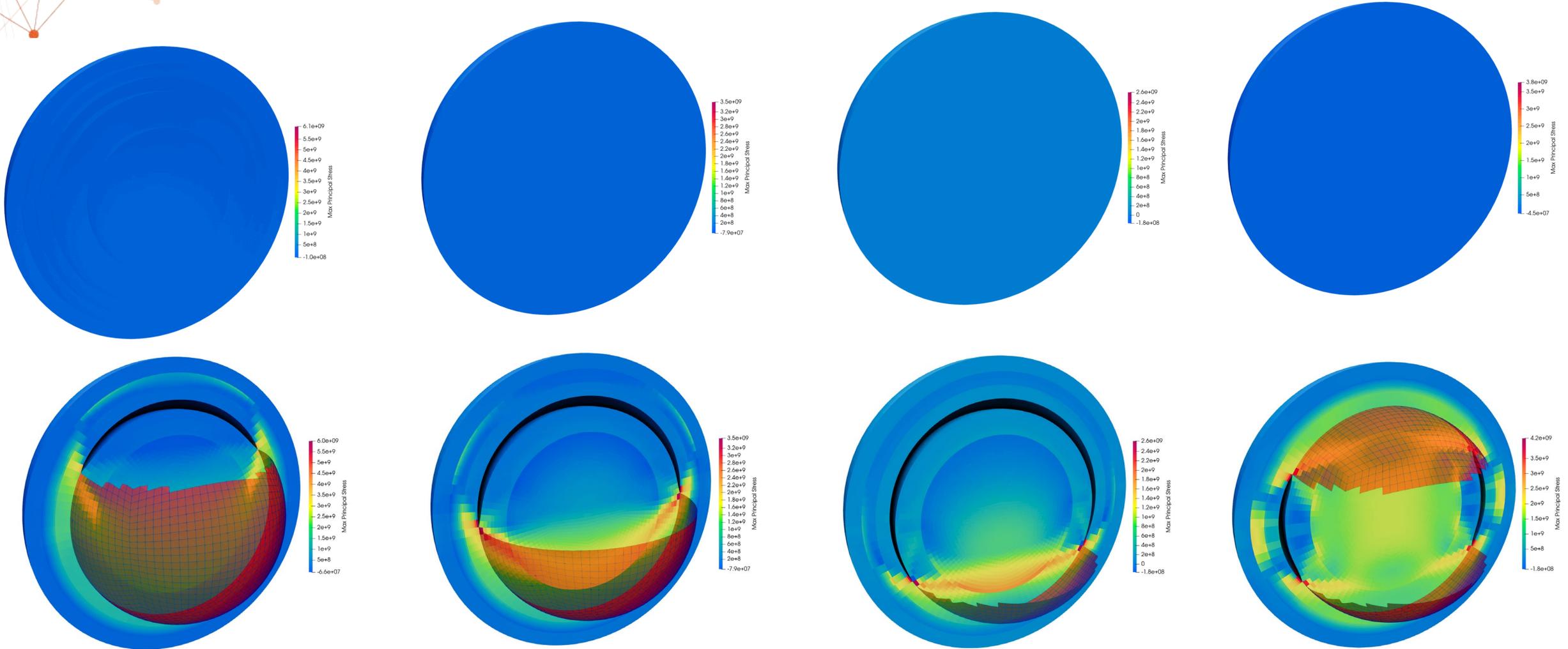


**Type Bi**



**Type Bf**

# Buffer Partial Debonding



Case1:  
Max Principal Stress  $6e9Pa$

Case2:  
Max Principal Stress  $3.5e9Pa$

Case2:  
Max Principal Stress  $2.6e9Pa$

Case4:  
Max Principal Stress  $4.2e9Pa$

# Phase-field Fracture Modeling

$$\{\mathbf{u}, \Gamma\} = \arg \min_{\mathbf{u}, \Gamma} \Psi(\mathbf{u}, \nabla \mathbf{u}, \Gamma),$$

$$\text{subject to } \mathbf{u} = \mathbf{g}, \quad \forall \mathbf{x} \in \partial\Omega_D,$$

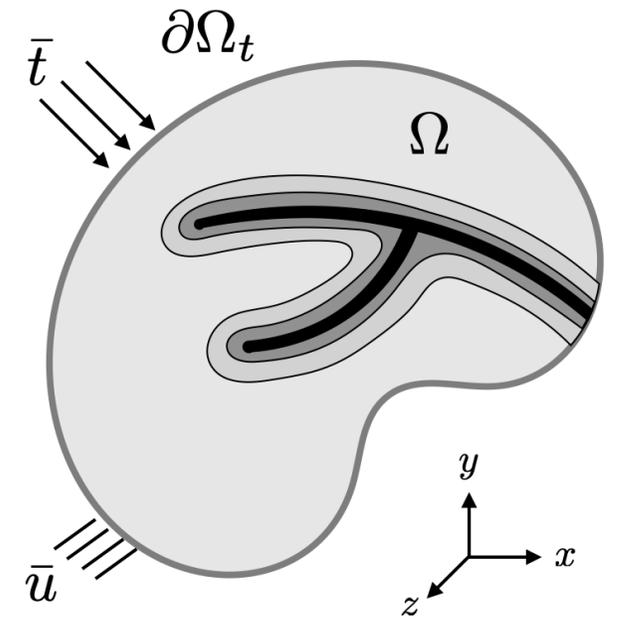
$$\Gamma(t) \subseteq \Gamma(t'), \quad \forall t' \in [t, T]$$

The objective function  $\Psi(\mathbf{u}, \nabla \mathbf{u}, \Gamma)$  is defined as:

$$\Psi(\mathbf{u}, \nabla \mathbf{u}, \Gamma) = \Psi_{\text{elastic}}(\nabla \mathbf{u}) + \Psi_{\text{fracture}}(\Gamma) - \Psi_{\text{dissipation}}(\mathbf{u}, \Gamma) - \Psi_{\text{external}}(\mathbf{u})$$

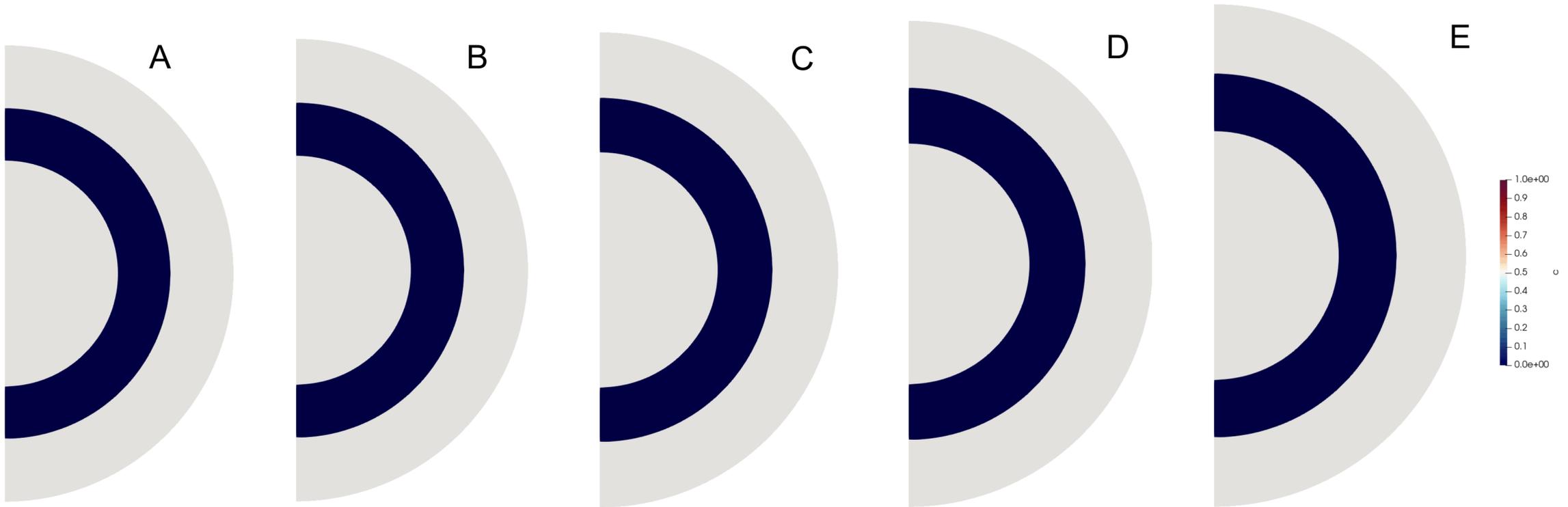
- Advantages of phase-field model

- Avoids re-meshing
- Determine crack nucleation and propagation automatically
- Handle joining and branching of multiple cracks



$$\Psi_{fracture}^l(c, \nabla c) = \int_{\Omega} \mathcal{G}_c \gamma_l(c, \nabla c) dV$$

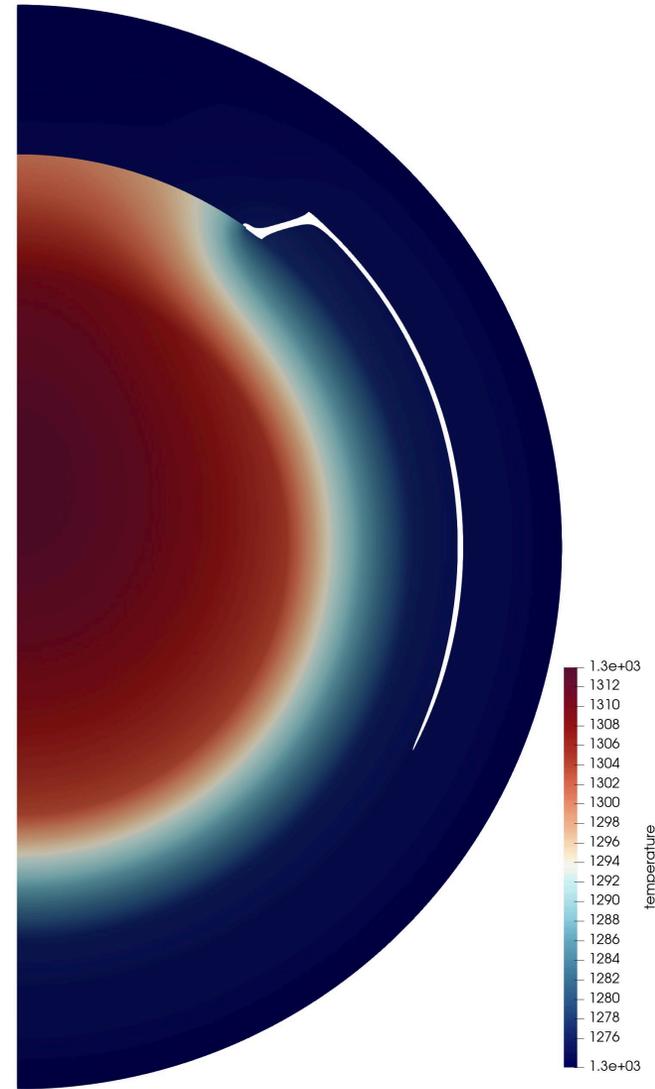
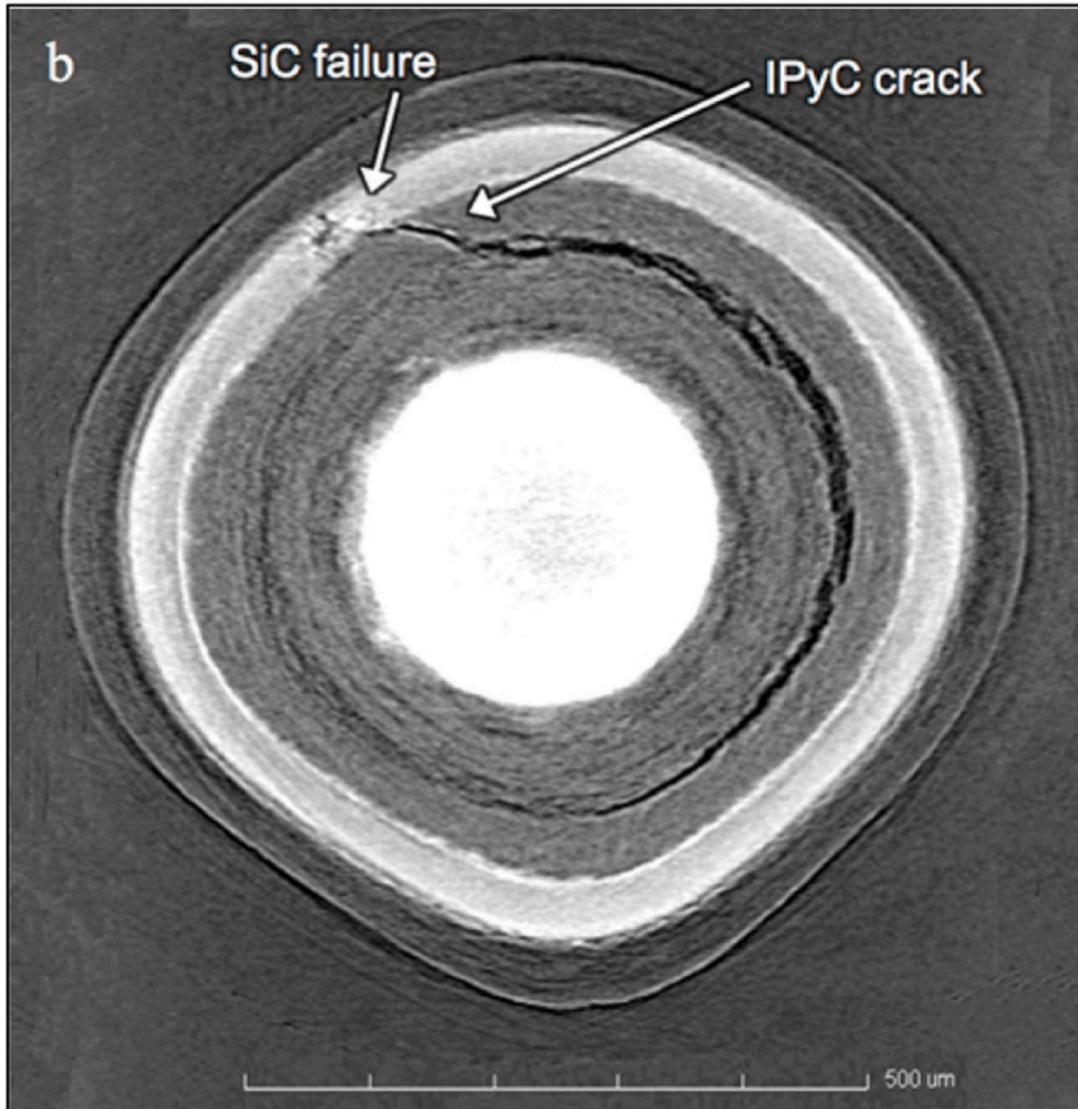
# Buffer Fracture Modeling



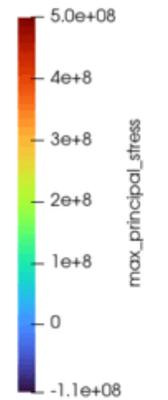
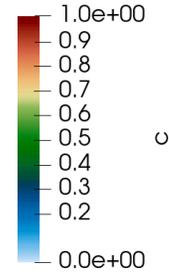
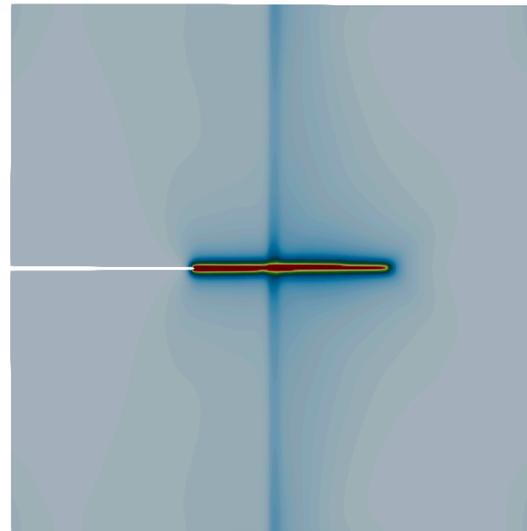
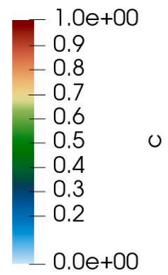
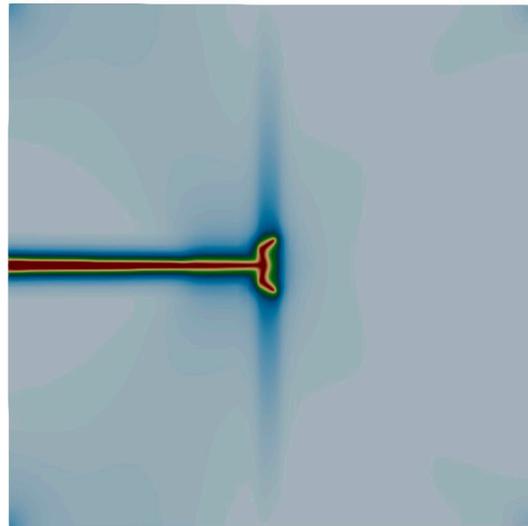
Bonding area:  $A > B > C$

Fracture Strength:  $D > A > E$

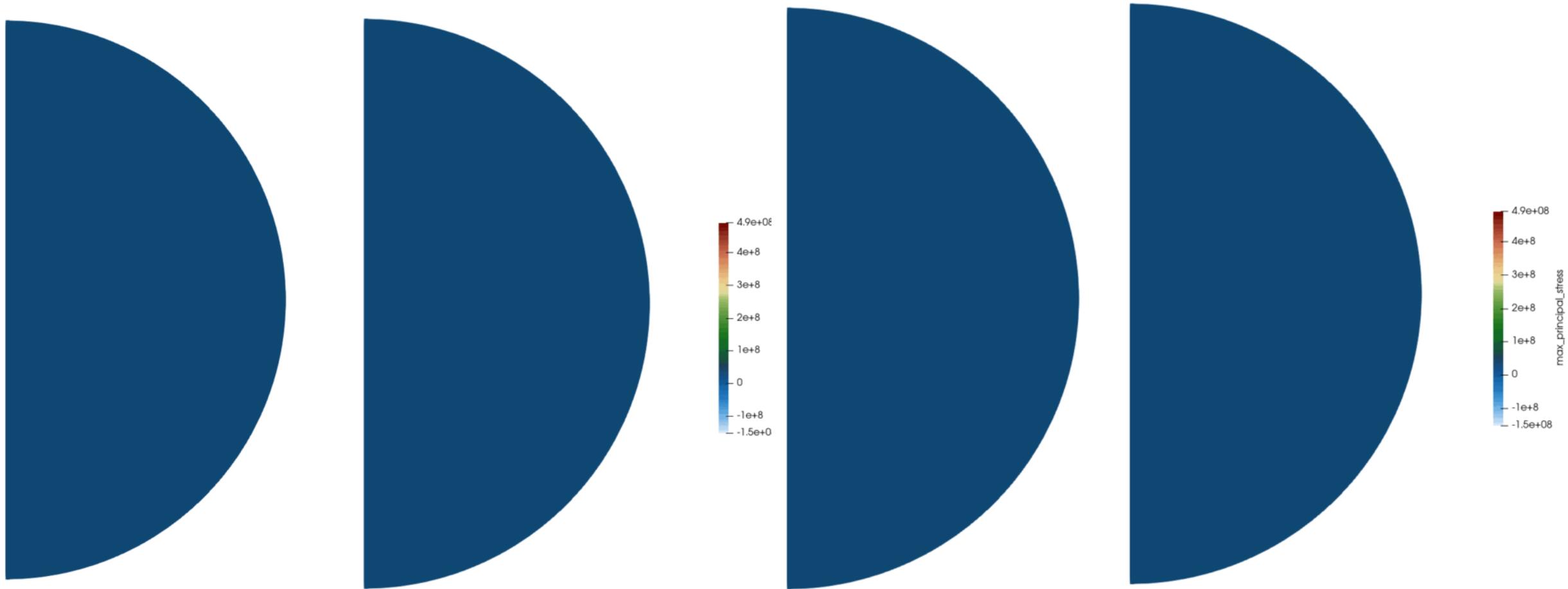
# Buffer and IPyC fracture modeling



# SiC fracture modeling



# TRISO coating layers fracture modeling



- Fracture stresses of buffer, IPyC and SiC were set to 300MPa, 300MPa and 400MPa respectively.